

The present invention which provides a method of fabricating a poly-poly capacitor using field effect transistor gate and bipolar SiGe extrinsic polysilicon layers will now be described in more detail by referring to the drawings that accompany the present application. It should be noted that in the drawings like and corresponding elements are referred to by like reference numerals.

IN THE CLAIMS:

Please cancel non-elected Claims 1-23, without prejudice or disclaimer, and please

amend Claims 24, 25 and 26 to read as follows:

*Sub. D* 24. (Amended) A poly-poly capacitor comprising upper and lower plate electrodes, wherein at least the upper plate electrode is composed of SiGe polysilicon, said plate electrodes being separated by an insulator structure.

*Sub. D* 25. (Amended) The poly-poly capacitor of Claim 24 wherein the lower plate electrode is composed of polysilicon.

*Sub. D* 26. (Amended) The poly-poly capacitor of Claim 24 wherein the lower plate electrode is composed of SiGe polysilicon.

REMARKS

Favorable reconsideration and allowance of the claims of the present application are respectfully requested.

Before addressing the specific grounds of rejection raised in the present Office Action, applicants have amended the specification and Claims 24, 25 and 26 in the manner indicated supra. Specifically, applicants have amended Claim 24 to positively recite that the claimed capacitor includes upper and lower plate electrodes wherein at least the upper plate electrode is composed of SiGe polysilicon. Support for this amendment to Claim 24 is seen in FIG 3, for example, where reference numeral 26 denotes the lower plate electrode and reference